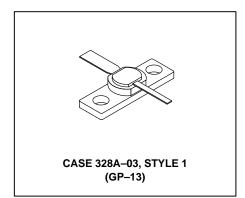
The RF Line Microwave Power Transistors

Designed primarily for large–signal output and driver amplifier stages in the 1.0 to 2.3 GHz frequency range.

- Designed for Class B or C, Common Base Power Amplifiers
- Specified 28 Volt, 2.0 GHz Characteristics: Output Power — 1.0 to 20 Watts Power Gain — 5.2 to 9.0 dB, Min Collector Efficiency — 40%, Min
- · Gold Metallization for Improved Reliability
- · Diffused Ballast Resistors
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRW2001 MRW2003

5.2-9.0 dB 1.0-2.3 GHz 1.0-20 W MICROWAVE POWER TRANSISTORS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Base Voltage	VCES	50	Vdc
Emitter-Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Continuous MRW2001 MRW2003	lc	0.25 0.5	Adc
Operating Junction Temperature	TJ	200	°C
Storage Temperature Range	T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, RF, Junction to Case MRW2001 MRW2003	R _θ JC	25 15	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Іур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage		V(BR)CES				Vdc
$(I_C = 10 \text{ mA}, V_{BE} = 0)$	MRW2001	` ′	50	_	_	
$(I_C = 20 \text{ mA}, V_{BE} = 0)$	MRW2003		50	_	_	

(continued)



ELECTRICAL CHARACTERISTICS — **continued** ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS (continued)						
Emitter–Base Breakdown Voltage ($I_E = 0.2 \text{ mA}, I_C = 0$) ($I_E = 0.25 \text{ mA}, I_C = 0$)	MRW2001 MRW2003	V _{(BR)EBO}	3.5 3.5	_ _	_ _	Vdc
Collector Cutoff Current (VCB = 28 V, IE = 0)	MRW2001 MRW2003	ICBO	_ _		0.5 0.5	mAdc
ON CHARACTERISTICS						
DC Current Gain (I _C = 100 mA, V _{CE} = 5.0 V) (I _C = 100 mA, V _{CE} = 5.0 V)	MRW2001 MRW2003	hFE	10 10		120 100	_
DYNAMIC CHARACTERISTICS						
Output Capacitance (V _{CB} = 28 V, I _E = 0, f = 1.0 MHz)	MRW2001 MRW2003	C _{ob}	_ _	_ _	4.0 5.0	pF
FUNCTIONAL TESTS						
Common–Base Amplifier Power Gain (V _{CE} = 28 V, P _{OUt} = 1.0 W, f = 2.0 GHz)	MRW2001	G _{PB}	9.0	_	_	dB
Common–Base Amplifier Power Gain (V _{CE} = 28 V, P _{out} = 3.0 W, f = 2.0 GHz)	MRW2003	G _{PB}	8.0	_	_	dB
Collector Efficiency (VCE = 28 V, P _{out} = 1.0 W, f = 2.0 GHz) (VCE = 28 V, P _{out} = 3.0 W, f = 2.0 GHz)	MRW2001 MRW2003	η	40	_	_	%
Load Mismatch (VCE = 28 V, f = 2.0 GHz, Load VSWR = ∞ :1, All Pout = 1.0 W Pout = 3.0 W	Phase Angles) MRW2001 MRW2003	Ψ	No Degradation in Output Power			
Saturated Output Power (VCE = 28 V, f = 2.3 GHz) (VCE = 28 V, f = 1.5 GHz) (VCE = 28 V, f = 1.0 GHz)	MRW2001	P _{sat1} P _{sat2} P _{sat3}	_ _ _	1.0 1.2 1.3	_ _ _	W
(V _{CE} = 28 V, f = 2.3 GHz) (V _{CE} = 28 V, f = 1.5 GHz) (V _{CE} = 28 V, f = 1.0 GHz)	MRW2003		_ _ _	3.0 3.7 4.0	_ _ _	

TYPICAL CHARACTERISTICS

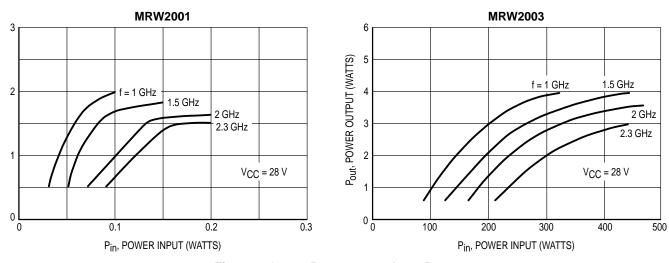


Figure 1. Output Power versus Input Power

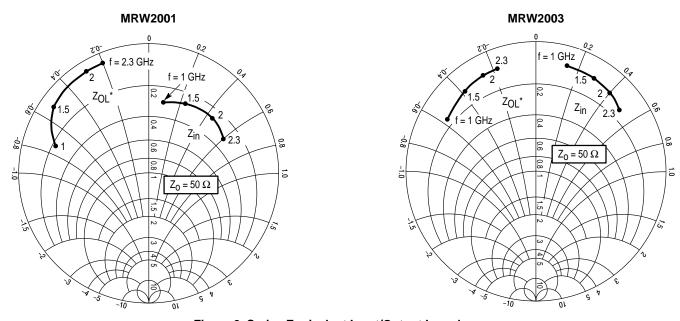


Figure 2. Series Equivalent Input/Output Impedance $V_{CC} = 28 \text{ V}$

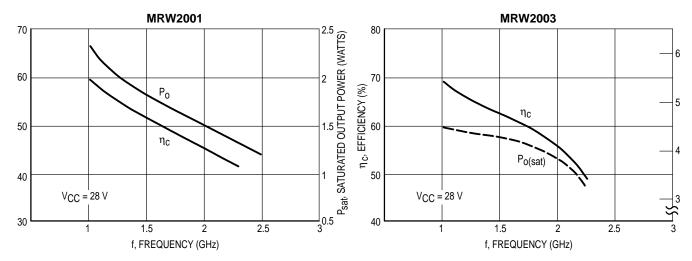


Figure 3. Power Output and Efficiency versus Frequency

The graph shown below displays MTTF in hours x ampere² emitter current for each of the "Super 2.0 GHz" devices. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ to the theoretical prediction for metal failure. Sample MTTF calculations based on operating conditions are included on the graph.

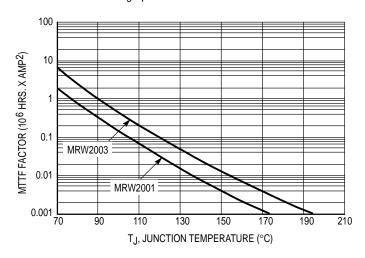


Figure 4. MTTF Factor

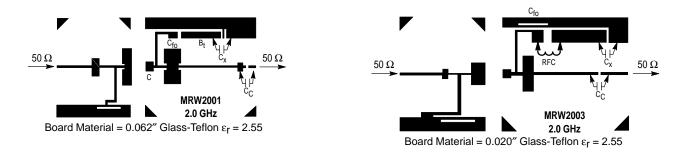
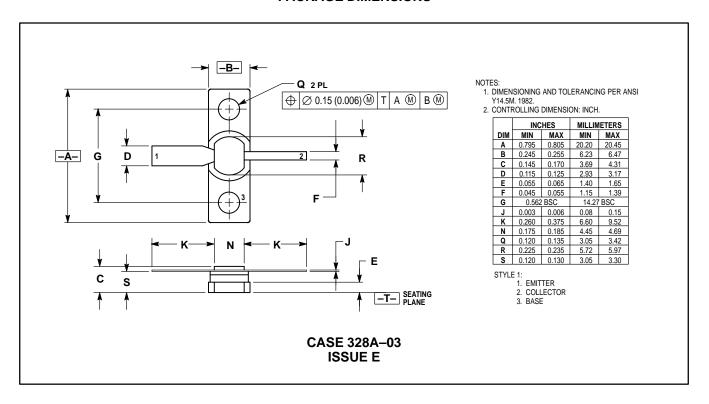


Figure 5. PC Board Layouts

PACKAGE DIMENSIONS



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